


 **o C b**  **(C)**
 **SFE - E**  **C,**
W

NVBG022N120M3S

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Case – Steady State (Note 2)	$R_{\theta JC}$	0.34	°C/W
Junction-to-Ambient – Steady State (Notes 1, 2)	$R_{\theta JA}$	40	

ELECTRICAL CHARACTERISTICS (T_J)

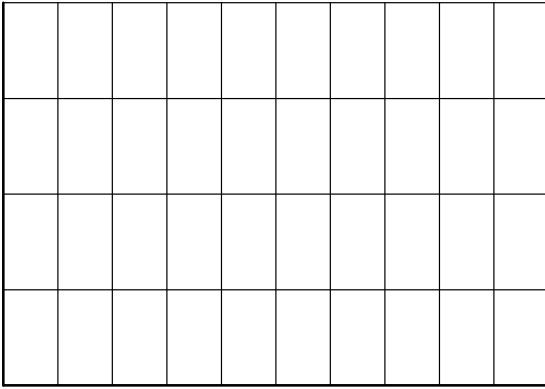
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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
SOURCE-DRAIN DIODE CHARACTERISTICS						
Reverse Recovery Time	t_{RR}	$V_{GS} = -3/18\text{ V}$, $I_{SD} = 40\text{ A}$, $di_S/dt = 1000\text{ A}/\mu\text{s}$, $V_{DS} = 800\text{ V}$ (Note 7)	–	23	–	ns
Reverse Recovery Charge	Q_{RR}		–	146	–	nC
Reverse Recovery Energy	E_{REC}		–	5	–	μJ
Peak Reverse Recovery Current	I_{RRM}		–	13	–	A
Charge time	t_A		–	13	–	ns
Discharge time	t					

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TYPICAL CHARACTERISTICS



V_{DS} , DRAIN-TO-
Figure 1. On-Region Characteristics

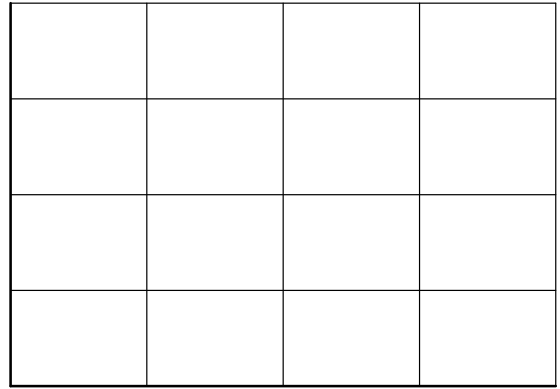
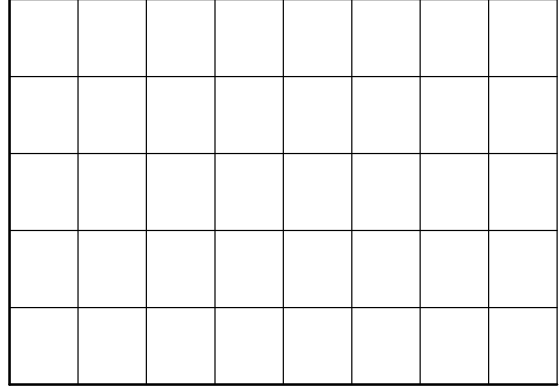
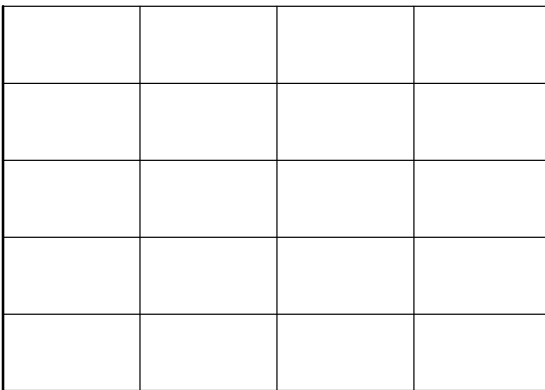
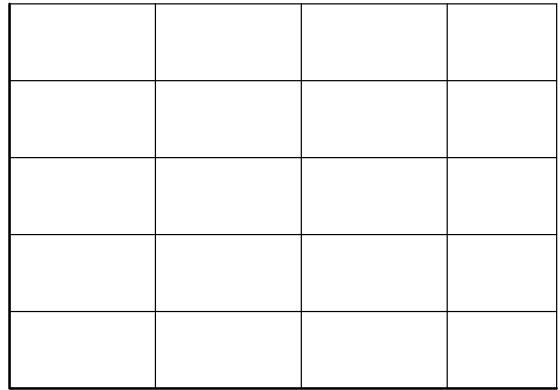
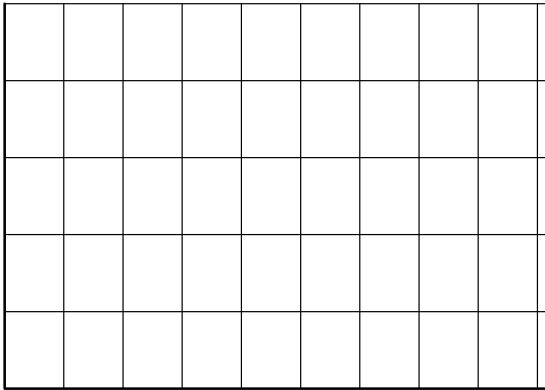


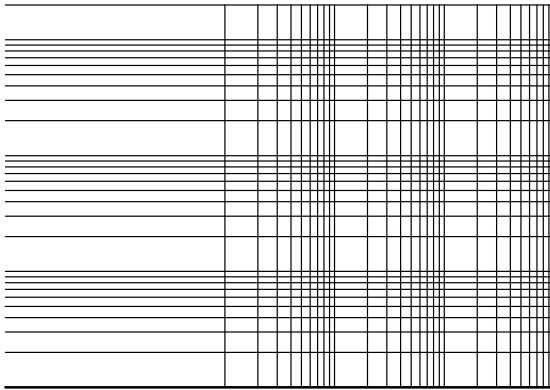
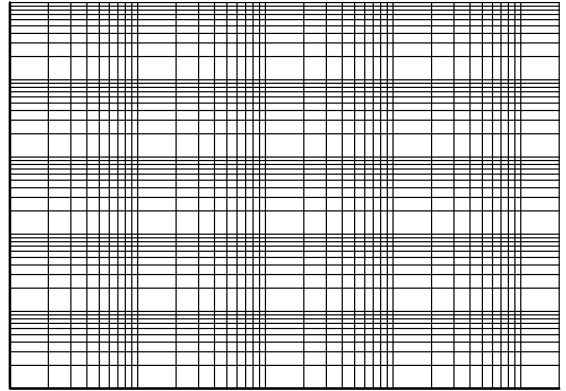
Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage



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TYPICAL CHARACTERISTICS



D²PAK7 (TO-263-7L HV)
CASE 418BJ
ISSUE B

DATE 16 AUG 2019

A

c2

H

C

**GENERIC
MARKING DIAGRAM***



XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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